

Abstract of the Disclosure:**MRAM WITH AN EFFECTIVE NOISE COUNTERMEASURE**

In a magnetic random access memory has a memory device portion (33,34,35) using magnetic material, a high-frequency current suppressor (26) is arranged in the vicinity of the magnetic material to suppress a high-frequency current which flows in the memory device portion. The memory device and the high-frequency current suppressor may be collectively molded in a mold body (25) of a plastic resin. It is preferable that the high-frequency current suppressor is made by a thin film of a granular magnetic material which has a composition represented by M-X-Y where M is a magnetic metal element, Y is one element selected from oxygen, nitrogen, and fluorine, and X is an element other than M and Y.

(Figs. 3 and 4)